

## Product Overview

### HGTG30N60B3: IGBT, 600V, PT

For complete documentation, see the data sheet.

The HGTG30N60B3 combines the best features of high input impedance of a MOSFET and the low on-state conduction loss of a bipolar transistor. The IGBT is ideal for many high voltage switching applications operating at moderate frequencies where low conduction losses are essential, such as UPS, solar inverter and power supplies.

### Features

- 30A, 600V,  $T_C = 110^\circ\text{C}$
- Low saturation voltage:  $V_{CE(sat)} = 1.45\text{V}$  @  $I_C = 30\text{A}$
- Typical Fall Time. . . . . 90ns at  $T_J = 150^\circ\text{C}$
- Short Circuit Rating
- Low Conduction Loss

### Applications

- Energy Generation & Distribution

### Part Electrical Specifications

Product	Compliance	Status	$V_{ES}$ Typ (V)	$I_C$ Max (A)	$V_{CE(sat)}$ Typ (V)	$V_F$ Typ (V)	$E_{off}$ Typ (mJ)	$E_{on}$ Typ (mJ)	$T_{rr}$ Typ (ns)	$I_{rr}$ Typ (A)	Gate Charge Typ (nC)	Short Circuit Withstand ( $\mu\text{s}$ )	$E_{AS}$ Typ (mJ)	$P_D$ Max (W)	Co- Pack aged Diode	Package Type
HGTG30N60B3	Pb-free	Active	600	30	1.45	-	0.68	0.5	-	-	170	-	100	208	No	TO-247-3

For more information please contact your local sales support at [www.onsemi.com](http://www.onsemi.com).

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